

Stanford

Ke Zeng

Postdoctoral Scholar, Electrical Engineering

Bio

BIO

Ke Zeng received his Ph.D. and MS degree in the Electrical Engineering Department of SUNY-Buffalo. His current research is focused on fabricating various high power/performance electronic devices based on GaN and Ga₂O₃, especially utilizing various novel edge termination techniques and device structures, as well as understanding the fundamental physics underlying these devices.

STANFORD ADVISORS

- Srabanti Chowdhury, Postdoctoral Faculty Sponsor

LINKS

- Personal Website: <http://web.stanford.edu/~kzeng2/>

Research & Scholarship

LAB AFFILIATIONS

- Srabanti Chowdhury, WBG-Lab (9/1/2019)

Publications

PUBLICATIONS

- **A discussion on various experimental methods of impact ionization coefficient measurement in GaN** *AIP ADVANCES*
Ji, D., Zeng, K., Bian, Z., Shankar, B., Gunning, B. P., Binder, A., Dickerson, J. R., Aktas, O., Anderson, T. J., Kaplar, R. J., Chowdhury, S.
2022; 12 (3)
- **On-Wafer Investigation of Avalanche Robustness in 1.3 kV GaN-on-GaN P-N Diode Under Unclamped Inductive Switching Stress**
Shankar, B., Zeng, K., Gunning, B., Lee, K., Martinez, R., Meng, C., Zhou, X., Flicker, J., Binder, A., Dickerson, J., Kaplar, R., Chowdhury, S., IEEE
IEEE.2021: 40-43
- **Study on Avalanche Uniformity in 1.2KV GaN Vertical PIN Diode with Bevel Edge-Termination**
Zeng, K., Chowdhury, S., Gunning, B., Kaplar, R., Anderson, T., IEEE
IEEE.2021
- **Designing Beveled Edge Termination in GaN Vertical p-i-n Diode-Bevel Angle, Doping, and Passivation** *IEEE TRANSACTIONS ON ELECTRON DEVICES*
Zeng, K., Chowdhury, S.
2020; 67 (6): 2457–62
- **Field-Plated Lateral Ga₂O₃ MOSFETs With Polymer Passivation and 8.03 kV Breakdown Voltage** *IEEE ELECTRON DEVICE LETTERS*
Sharma, S., Zeng, K., Saha, S., Singiseti, U.
2020; 41 (6): 836–39